

## 研究業績

### (1) 学術論文

#### 1. Seiji Samukawa

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## **(2)学位論文**

「電子サイクロトロン共鳴プラズマ法による半導体サブミクロン加工に関する研究」  
博士（工学、慶應義塾大学）平成4年2月5日

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**(7) 論文賞、学会賞、その他受賞**

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Outstanding Paper Awards (論文賞): 寒川誠二、塚田勉
2. 1998 年石黒賞 (NEC 功績賞): 寒川誠二
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## (9) 社外組織との関わり

### 9-1 共同研究

1. 名古屋大学工学研究科量子工学専攻; 後藤俊夫教授 (UHF プラズマ、ラジカル計測、微粒子)
2. 静岡大学理学部物理学科; 三重野哲助教授 (負イオン計測、パルス変調プラズマ)
3. 防衛大学電気工学教室; 中野俊樹助教授 (UHF プラズマ、イオン速度分布計測)
4. Lucent Technologies, Bell Laboratories, USA; Dr. Vincent M. Donnelly  
(UHF plasma, Pulsed Plasma).
5. Universite Joseph Fourier and CNRS, France; Prof. N. Sadeghi  
(UHF Plasma, Ion Velocity).

### 9-2. 学会役員

1. 応用物理学会プラズマエレクトロニクス分科会幹事 (1992-1994) 副幹事長(2000-2002).
2. 応用物理学会学会誌編集委員 (1994-1996).
3. 国際マイクロプロセスコンファレンス論文委員  
(応用物理学会、1993-1997, 1996-97: セクションヘッド, 2000-).
4. ドラプロセスシンポジウム論文委員(電気学会、1994-, 1996: 副委員長,  
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8. 電気学会専門調査委員会 ”非平衡プラズマのモデリングと微細加工” 幹事(1997年-2002年).
9. 電気学会電子衝突断面積専門調査委員会、委員 (1995年-).
10. American Vacuum Society, program committee (1997年-2002年)  
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11. International Symposium on Electron-Molecule Collisions and Swarms,  
organizing committee (物理学会原子衝突協会、1998年-).
12. International Workshop on Basic Aspect of non-equilibrium Plasma and Interaction with Surface,  
Organizing committee (JSAP、1999年-).
13. 応用物理学会シリコンテクノロジー分科会幹事 (2002年、2004-2006年)
14. 応用物理学会代議員 (2002年)
15. 機械学会東北支部商議員 (2003年-)

以上